MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK62J60W

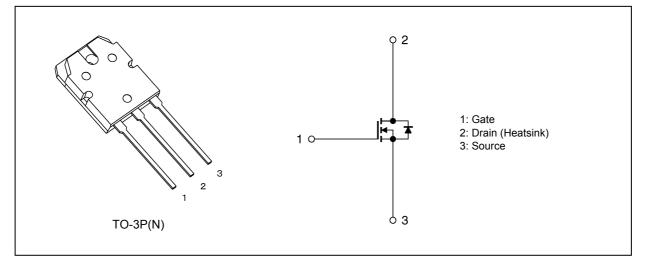
#### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.033 \Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.7 to 3.7 V ( $V_{\rm DS}$  = 10 V,  $I_{\rm D}$  = 3.1 mA)

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

| Characteristics                     |          |                  | Rating     | Unit  |
|-------------------------------------|----------|------------------|------------|-------|
| Drain-source voltage                |          | V <sub>DSS</sub> | 600        | V     |
| Gate-source voltage                 |          | V <sub>GSS</sub> | ±30        |       |
| Drain current (DC)                  | (Note 1) | I <sub>D</sub>   | 61.8       | A     |
| Drain current (pulsed)              | (Note 1) | I <sub>DP</sub>  | 247        |       |
| Power dissipation (T <sub>c</sub> = | 25°C)    | PD               | 400        | W     |
| Single-pulse avalanche energy       | (Note 2) | E <sub>AS</sub>  | 698        | mJ    |
| Avalanche current                   |          | I <sub>AR</sub>  | 15.5       | A     |
| Reverse drain current (DC)          | (Note 1) | I <sub>DR</sub>  | 61.8       |       |
| Reverse drain current (pulsed)      | (Note 1) | I <sub>DRP</sub> | 247        |       |
| Channel temperature                 |          | T <sub>ch</sub>  | 150        | °C    |
| Storage temperature                 |          | T <sub>stg</sub> | -55 to 150 | 7     |
| Mounting torque                     |          | TOR              | 0.8        | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2012-09

#### 5. Thermal Characteristics

| Characteristics                       |                       | Max   | Unit |
|---------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance    | R <sub>th(ch-c)</sub> | 0.313 | °C/W |
| Channel-to-ambient thermal resistance | R <sub>th(ch-a)</sub> | 50    |      |

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V\_DD = 90 V, T\_ch = 25°C (initial), L = 5.08 mH, R\_G = 25  $\Omega$ , I\_AR = 15.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

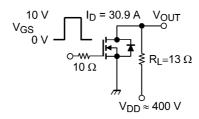
#### 6. Electrical Characteristics

### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

| Characteristics                | Symbol               | Test Condition                                  | Min | Тур.  | Max   | Unit |
|--------------------------------|----------------------|---|-----|-------|-------|------|
| Gate leakage current           | I <sub>GSS</sub>     | $V_{GS}$ = ±30 V, $V_{DS}$ = 0 V                | _   | _     | ±1    | μA   |
| Drain cut-off current          | I <sub>DSS</sub>     | V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V  | _   | _     | 10    |      |
| Drain-source breakdown voltage | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V   | 600 | —     | —     | V    |
| Gate threshold voltage         | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.1 mA | 2.7 | _     | 3.7   |      |
| Drain-source on-resistance     | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30.9 A |     | 0.033 | 0.040 | Ω    |

### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                | Symbol             | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------|--------------------|---|-----|------|-----|------|
| Input capacitance              | C <sub>iss</sub>   | V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz | _   | 6500 | _   | pF   |
| Reverse transfer capacitance   | C <sub>rss</sub>   | ]   | _   | 20   | _   |      |
| Output capacitance             | C <sub>oss</sub>   |   | _   | 140  | _   |      |
| Effective output capacitance   | C <sub>o(er)</sub> | $V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V                       | _   | 200  | _   |      |
| Gate resistance                | r <sub>g</sub>     | V <sub>DS</sub> = OPEN, f = 1 MHz                           | _   | 2    | _   | Ω    |
| Switching time (rise time)     | t <sub>r</sub>     | See Figure 6.2.1  | _   | 58   | _   | ns   |
| Switching time (turn-on time)  | t <sub>on</sub>    | ]   | _   | 115  | _   |      |
| Switching time (fall time)     | t <sub>f</sub>     | ]   | _   | 15   | _   |      |
| Switching time (turn-off time) | t <sub>off</sub>   | ]   | _   | 310  |     |      |
| MOSFET dv/dt ruggedness        | dv/dt              | V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 15.5 A       | 50  | _    | _   | V/ns |



Duty  $\leq$  1%,  $t_W^{}=$  10  $\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V},  V_{GS} \text{ = } 10  \text{V},  \text{I}_{D} \text{ = } 61.8  \text{A}$ | —   | 180  | —   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | _   | 38   | _   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  | _   | 85   | _   |      |

### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics               | Symbol           | Test Condition                                      | Min | Тур. | Max  | Unit |
|-------------------------------|------------------|---|-----|------|------|------|
| Diode forward voltage         | V <sub>DSF</sub> | I <sub>DR</sub> = 61.8 A, V <sub>GS</sub> = 0 V     | _   | _    | -1.7 | V    |
| Reverse recovery time         | t <sub>rr</sub>  | I <sub>DR</sub> = 30.9 A, V <sub>GS</sub> = 0 V     | _   | 500  | _    | ns   |
| Reverse recovery charge       | Q <sub>rr</sub>  | -dI <sub>DR</sub> /dt = 50 A/μs                     | _   | 7    | _    | μC   |
| Peak reverse recovery current | l <sub>rr</sub>  |   | _   | 25   | _    | А    |
| Diode dv/dt ruggedness        | dv/dt            | $I_{DR}$ = 30.9 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V | 15  | _    | _    | V/ns |

### 7. Marking (Note)

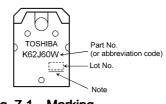
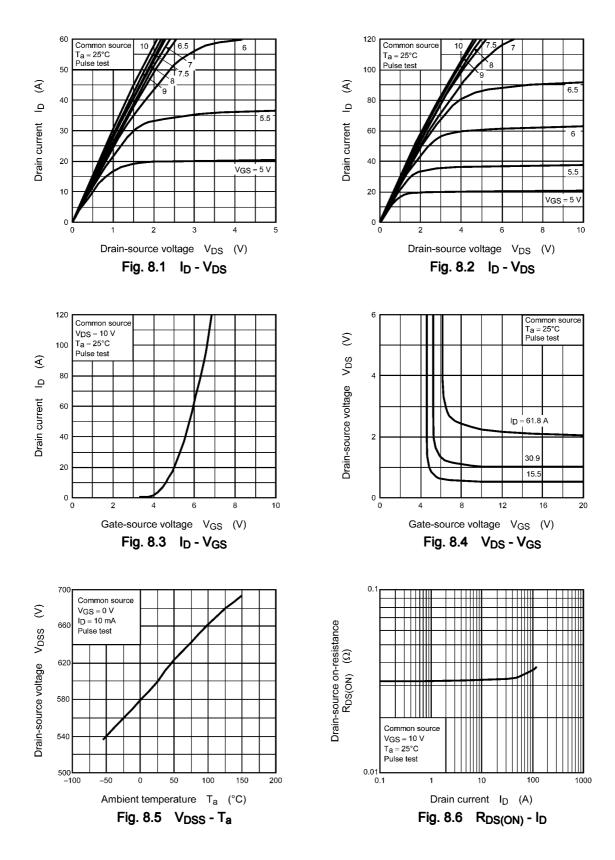
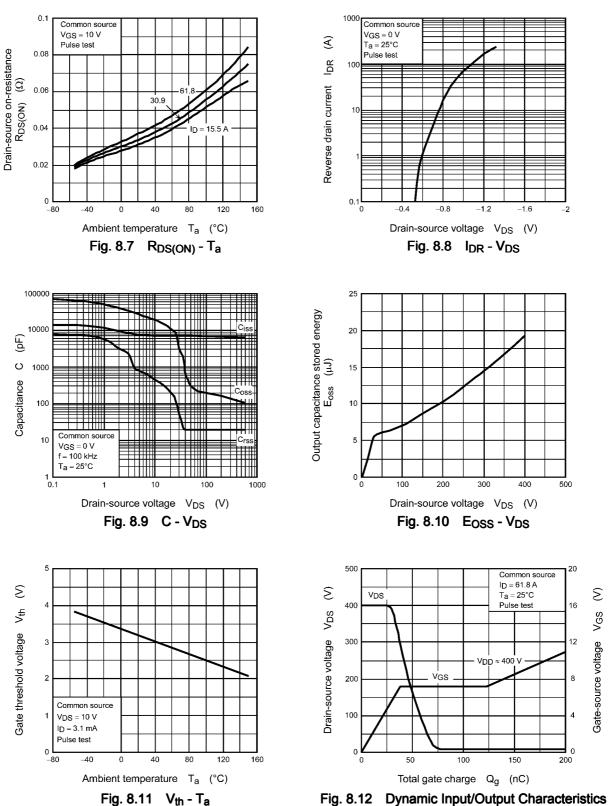


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

### 8. Characteristics Curves (Note)





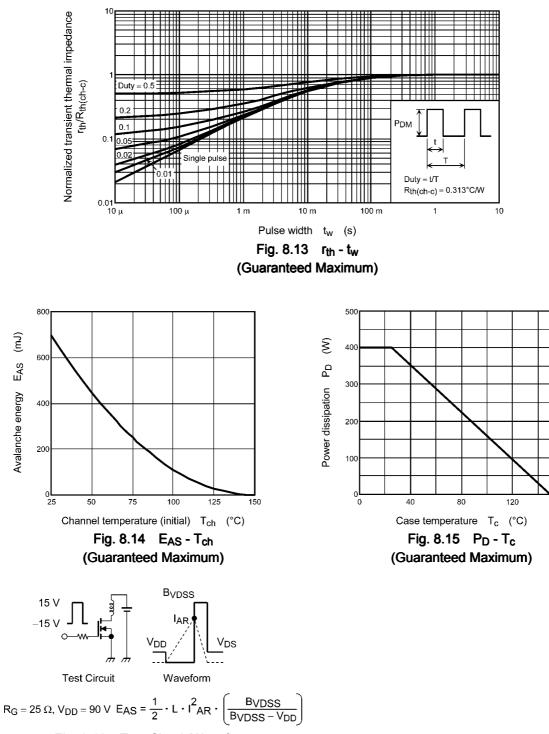
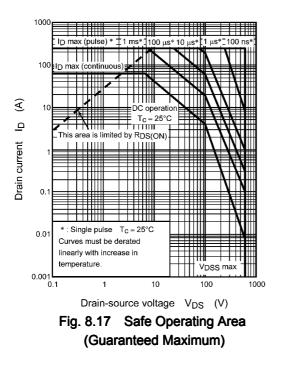


Fig. 8.16 Test Circuit/Waveform

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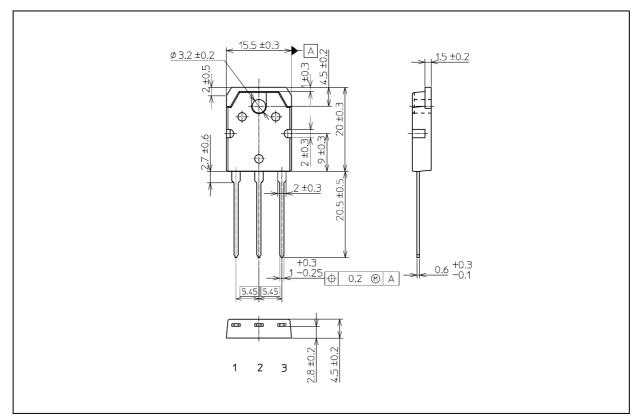


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### TK62J60W

### Package Dimensions

Unit: mm



### Weight: 4.6 g (typ.)

| Package Name(s)    |  |
|--------------------|--|
| JEITA: SC-65       |  |
| TOSHIBA: 2-16C1S   |  |
| Nickname: TO-3P(N) |  |

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